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### Abstract

**PURPOSE:**To contrive to improve the long-term stability of a semiconductor device by a method wherein at least one of regions of three kinds of concentrations is made to overlap with a gate electrode.  
**CONSTITUTION:**When P<+> is implanted in a silicon oxide film 4 by an ion implantation method, the incident angle of the P<+> is slanted from a perpendicular plane erected on a gate electrode 3 to the left and diffused regions are formed so as to become a source and gate overlapping region 5a and a drain and gate offset region 5b. Then, when the incident angle is slanted from the perpendicular plane to the right and P<+> is implanted, the diffusion phenomenon of the phosphorus impurity in the regions 5a and 5b is caused and a gate overlapping region 6b having two concentration profiles, a high-concentration drain region 7b due to the P<+> and a high-concentration source region 7a due to the region 5a and the P<+> are formed. Then, sidewalls 8 are respectively formed on the side surfaces of the gate electrode 3 by etching, then, a high-concentration source region 9a and a high-concentration drain region 9b are formed by an ion implantation. In such a way, the amounts of overlap of the electrode 3 with the region 5a and the electrode 3 with the region 6b can be reliably obtained, an electric field is relaxed in diffused regions having three concentration profiles and the long-term stability of a semiconductor device is enhanced.

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### CLAIMS

No Claims were found.

### DESCRIPTION

Text Not Available.